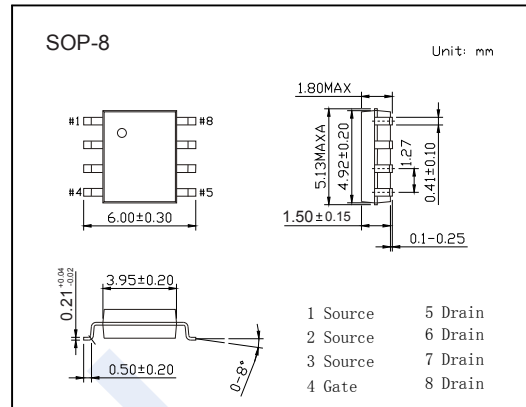
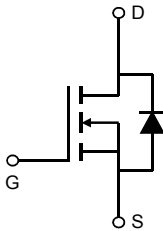


N-Channel MOSFET

AO4260-HF (KO4260-HF)

■ Features

- $V_{DS} (V) = 60V$
- $I_D = 18 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 5.2m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 6.3m\Omega (V_{GS} = 4.5V)$
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ C$	18
		$T_A=70^\circ C$	14
Pulsed Drain Current	I_{DM}	130	A
Avalanche Current	I_{AS}	65	A
Avalanche energy	$L=0.1mH$	EAS	211
Power Dissipation	P_D	$T_A=25^\circ C$	3.1
		$T_A=70^\circ C$	2
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40
		Steady-State	75
Thermal Resistance.Junction- to-Lead	R_{thJL}	24	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

N-Channel MOSFET

AO4260-HF (KO4260-HF)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 uA, V _{GS} =0V	60			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{Ds} =60V, V _{GS} =0V			1	uA	
		V _{Ds} =60V, V _{GS} =0V, T _J =55°C			5		
Gate-Body Leakage Current	I _{GSS}	V _{Ds} =0V, V _{GS} =±20V			±100	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{Ds} =V _{GS} , I _D =250uA	1.3		2.4	V	
Static Drain-Source On-Resistance	R _{Ds(on)}	V _{GS} =10V, I _D =18A			5.2	mΩ	
		V _{GS} =10V, I _D =18A T _J =125°C			8.4		
		V _{GS} =4.5V, I _D =16A			6.3		
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{Ds} =5V	130			A	
Forward Transconductance	g _{FS}	V _{Ds} =5V, I _D =18A		70		S	
Input Capacitance	C _{iss}	V _{GS} =0V, V _{Ds} =30V, f=1MHz		4940		pF	
Output Capacitance	C _{oss}			445			
Reverse Transfer Capacitance	C _{rss}			32			
Gate Resistance	R _g	V _{GS} =0V, V _{Ds} =0V, f=1MHz	0.4		1.4	Ω	
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{Ds} =30V, I _D =18A		71	100	nC	
Total Gate Charge (4.5V)				31	45		
Gate Source Charge			Q _{gs}		12.5		
Gate Drain Charge			Q _{gd}		8.5		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{Ds} =30V, R _L =1.67Ω, R _{GEN} =3Ω		8.5		ns	
Turn-On Rise Time	t _r			8.5			
Turn-Off DelayTime	t _{d(off)}			50			
Turn-Off Fall Time	t _f			15.5			
Body Diode Reverse Recovery Time	t _{rr}	I _F = 18A, di/dt= 500A/us		22		nC	
Body Diode Reverse Recovery Charge	Q _{rr}			96			
Maximum Body-Diode Continuous Current	I _S				4.5	A	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V	

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4260 KC**** _F
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N-Channel MOSFET AO4260-HF (KO4260-HF)

■ Typical Characteristics

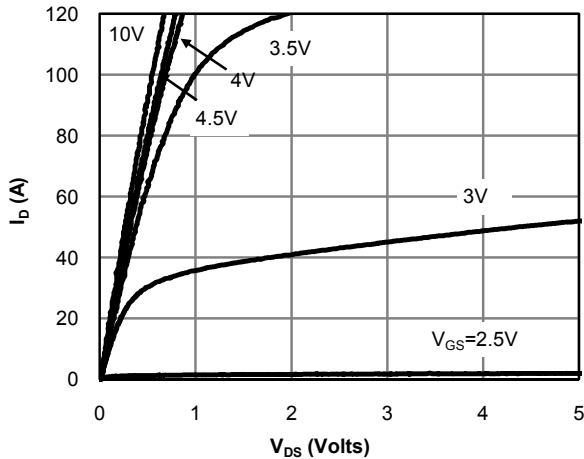


Fig 1: On-Region Characteristics (Note E)

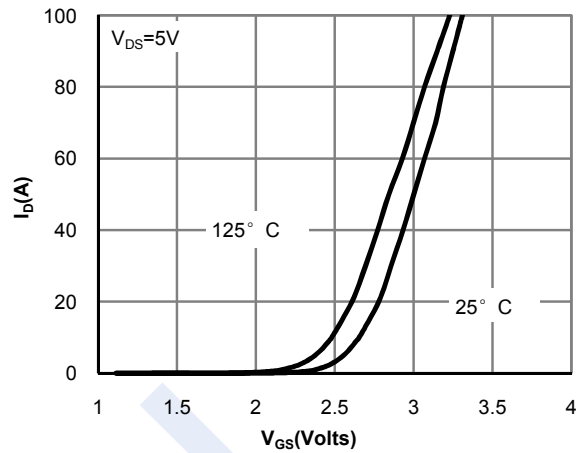


Figure 2: Transfer Characteristics (Note E)

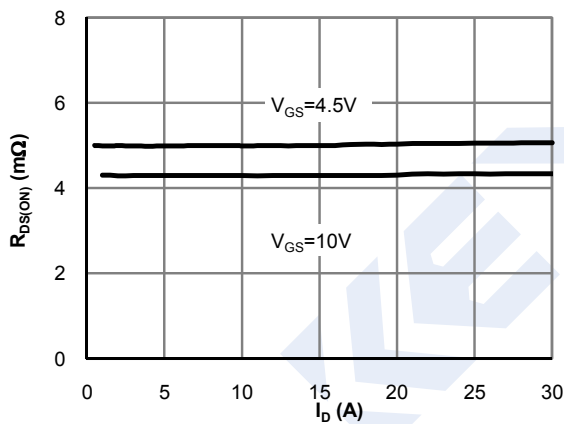


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

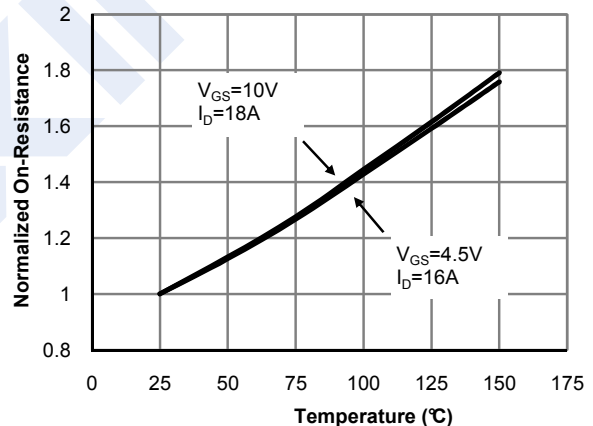


Figure 4: On-Resistance vs. Junction Temperature (Note E)

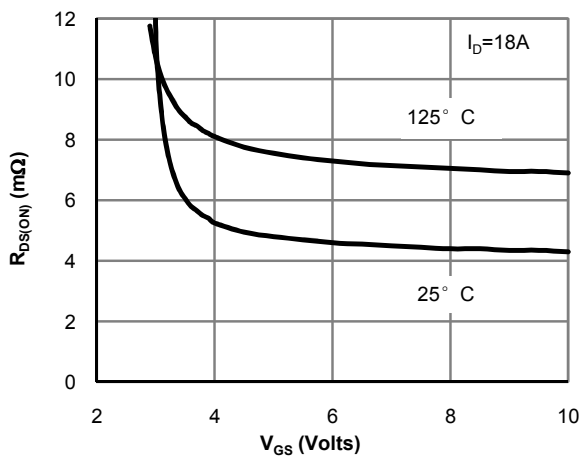


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

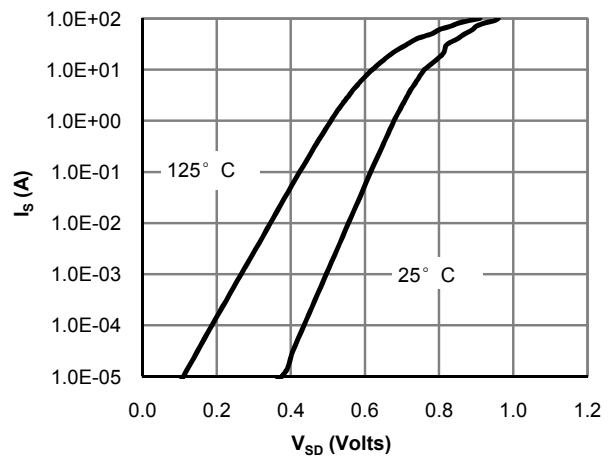


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET AO4260-HF (KO4260-HF)

■ Typical Characteristics

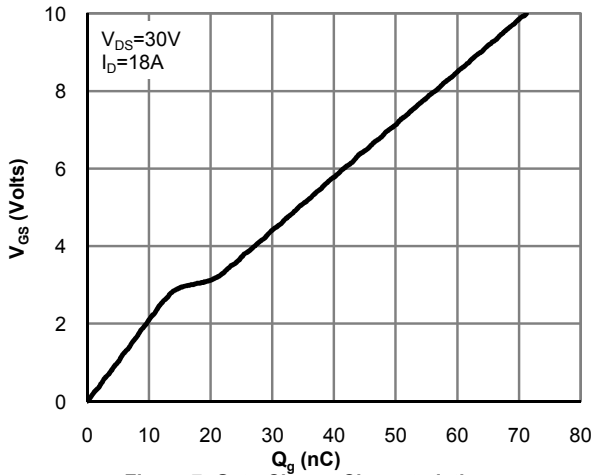


Figure 7: Gate-Charge Characteristics

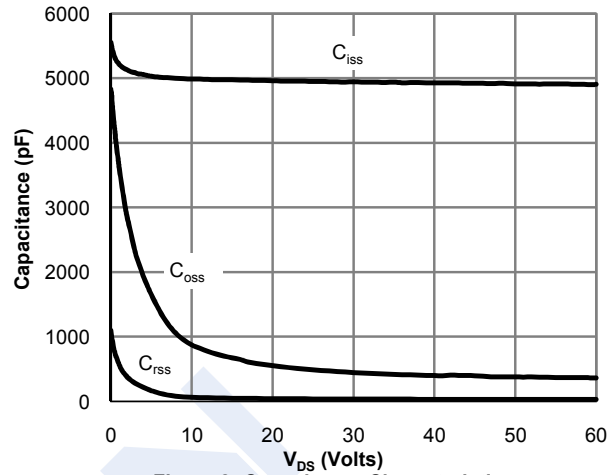


Figure 8: Capacitance Characteristics

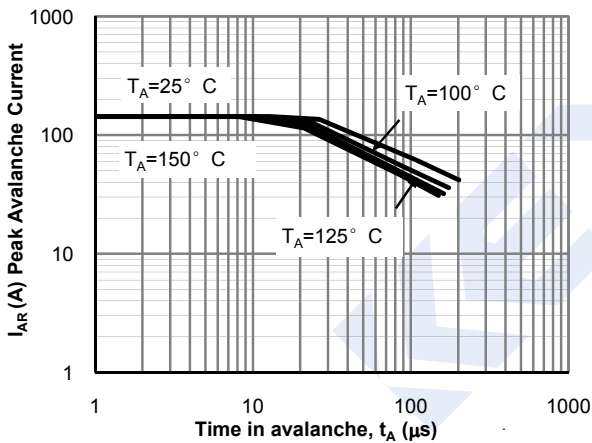


Figure 12: Single Pulse Avalanche capability (Note C)

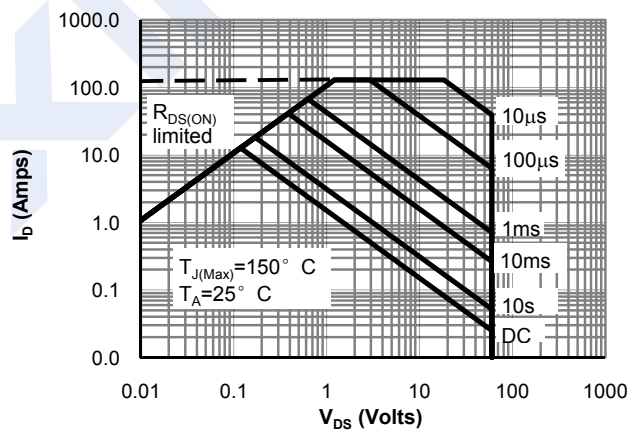


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

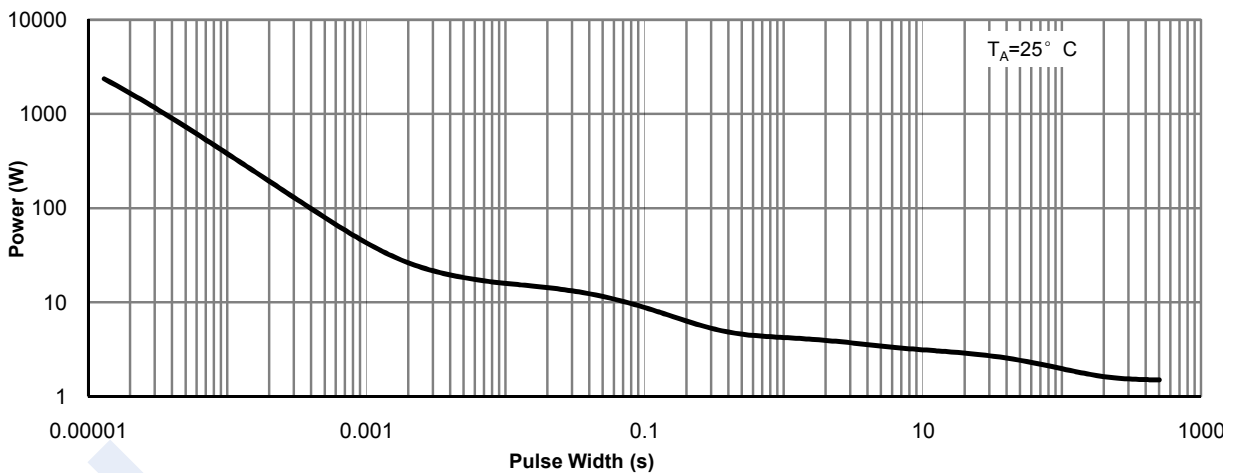


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET AO4260-HF (KO4260-HF)

■ Typical Characteristics

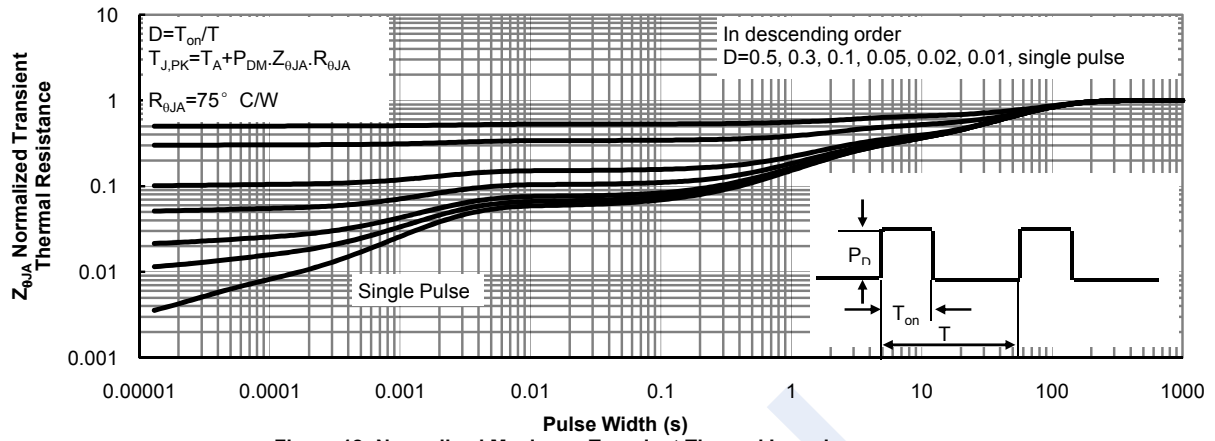


Figure 12: Normalized Maximum Transient Thermal Impedance s